

<p style="text-align: center;">INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p> <p style="text-align: center;">NOV 07 2003 JC42</p> <p style="text-align: center;">PATENT & TRADEMARK OFFICE</p>		ATTY DOCKET NO. ITO.0549US (P16246)		SERIAL NO. 10/634,146		
		APPLICANT(S): BRIAN G. JOHNSON				
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		U.S. PATENT DOCUMENTS				
EXAMINER TRADENAME	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.					
	B.					
	C.					
	D.					
FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
E.						
F.						
G.						
H.						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
MJW	I.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Jeong, U.I., Jeong, H.S. and Kim, Kinam, "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors," presented at 2003 19 th IEEE Non-Volatile Semiconductor Memory Workshop, Monterey, California, February 26-20, 2003				
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MJW	K.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Oh, J.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Chung, U.I., Jeong, H.S. and Kim, Kinam, "Full Integration and Reliability Evaluation of Phase-change RAM Based on 0.24 mm-CMOS Technologies," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003				
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/Michael Weinberg/ 06/20/2006